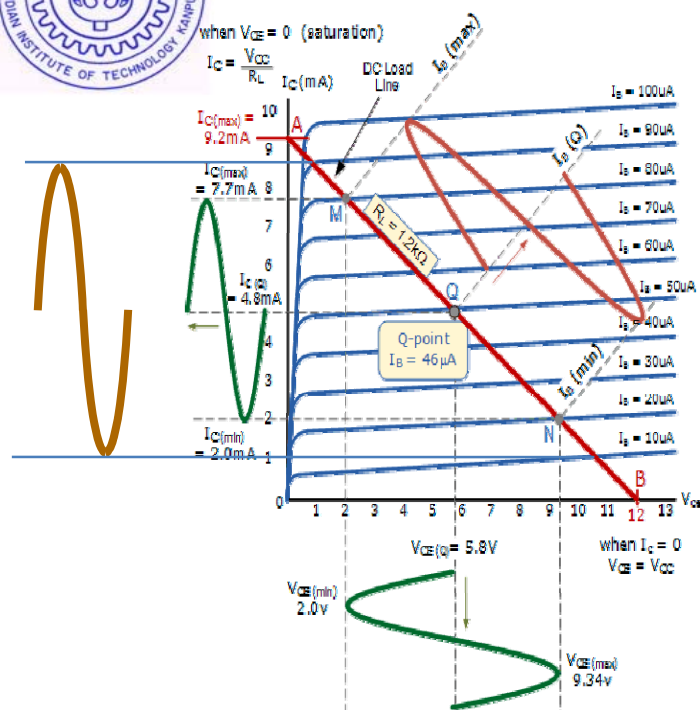




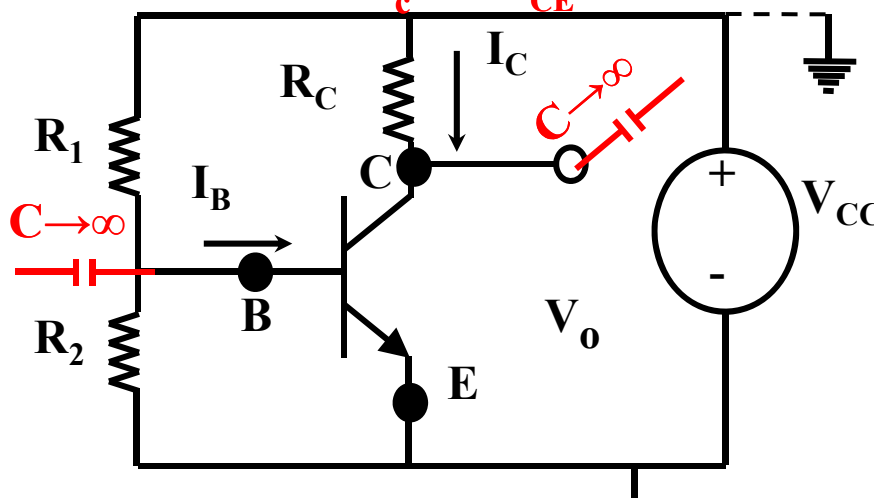
ESc201, Lecture 20: BJT Amplifier (Small signal Model)

$$V_{CEQ} = \frac{V_{CC} - 0.7}{2}$$



R_1 and R_2 that $I_B \ll I_2$. So that $I_1 \approx I_2$. Base current shouldn't disturb voltage divider action. Thus, Q-point is independent of base current as well as current gain.

Rule of thumb: Equal division of V_{CC} between R_C and V_{CE}

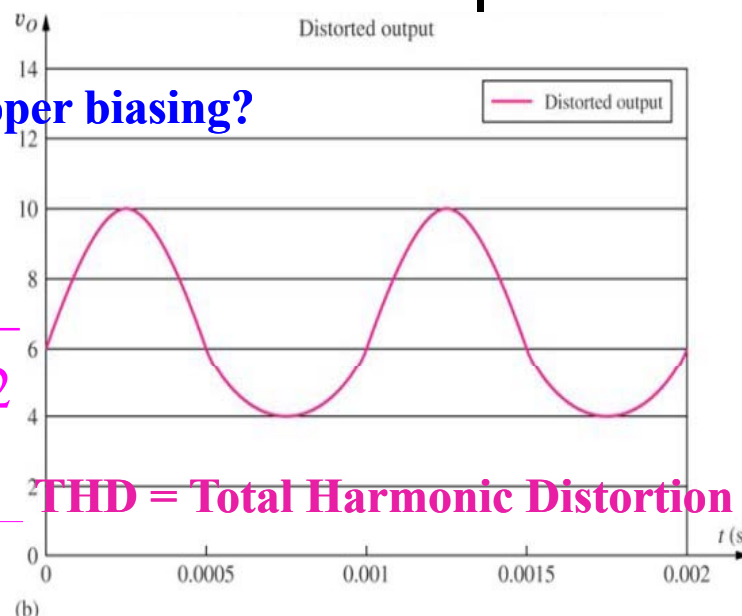


Why need to do proper biasing?

$$v(t) = V_0 + V_1(\sin\omega_0 t + \phi_1) + V_2(2\sin\omega_0 t + \phi_2) + V_3(3\sin\omega_0 t + \phi_3) + \dots$$

dc
 desired output
 2nd harmonic distortion
 3rd harmonic distortion
 Higher Order distortion

$$\text{THD} = 100\% \times \frac{\sqrt{\sum_{n=2}^{\infty} V_n^2}}{V_1}$$



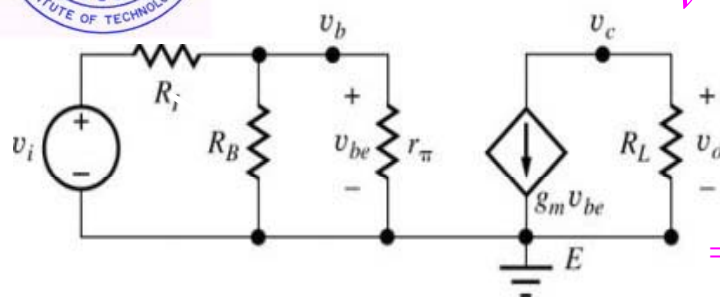
Numerator = sum of rms amplitudes of distortion terms, Denominator = desired component

But this design is not protected against Q-Point variation with β . So R_E is required for that.



ESc201, Lecture 20: Bipolar Junction Transistor (Small signal Model)

Without R_E



$$A_v = \frac{v_o}{v_i} = \left(\frac{v_o}{v_b} \right) \left(\frac{v_b}{v_i} \right) = - \frac{\beta i_b R_L}{i_b r_\pi} \left(\frac{v_b}{v_i} \right)$$

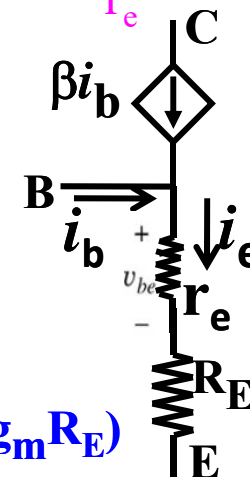
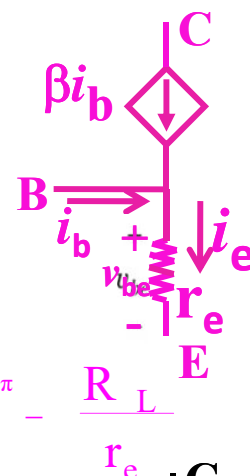
$$= - \frac{\beta R_L}{r_\pi} \frac{r_\pi}{\{R_i + r_\pi\}} = - \frac{\beta R_L}{\{R_i + r_\pi\}}$$

$$= - \frac{\beta R_L}{\{R_i + (\beta + 1)r_e\}} \cong - \frac{\beta R_L}{\{(\beta + 1)r_e\}} \quad R_i \ll r_\pi$$

$$A_v = - \frac{\beta R_L}{\{R_i + (\beta + 1)(r_e + R_E)\}} \quad R_i \ll r_\pi$$

Effect of adding R_E

1. The voltage gain is now less dependent on β .
2. The input resistance is increased by a factor of $(1 + g_m R_E)$.
3. The base to collector voltage gain is reduced by $1 / (1 + g_m R_E)$
4. For the same nonlinear distortion the input can be increased by factor of $(1 + g_m R_E)$
5. The frequency response is significantly improved.



As a particular example for $\beta=100$, $R_L=4.12\text{k}\Omega$, $R_E=300\Omega$, and a $C_{\text{Emitter-Collector}}=0.5\text{pF}$

Without R_E the values are :

$A_{\text{mid freq}} = -153$, $f_H = 1.56 \text{ MHz}$ (\sim Bandwidth), GBWP (Gain Bandwidth Product) = 239 MHz.

With R_E the values are :

$A_{\text{mid freq}} = -11.0$, $f_H = 13.9 \text{ MHz}$, GBWP = 153 MHz.

And R_{in} must have increased by approximately a ratio of $(153/11)=14$ times.





ESc201, Lecture 20: BJT Amplifier (Small signal Model)

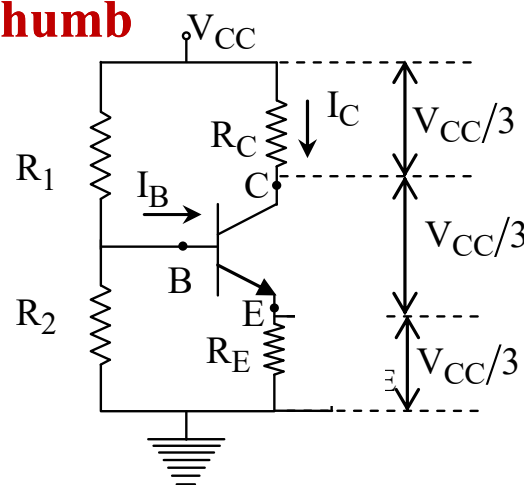
4-Resistor Bias Network for BJT - $V_{CC}/3$ Rule of Thumb

$$I_E = \frac{V_{BB} - V_{BE} - R_B I_B}{R_E} \cong \frac{V_{BB} - V_{BE}}{R_E} \quad \text{for } R_B I_B \ll (V_{BB} - V_{BE})$$

This implies that $I_B \ll I_2$. So that $I_1 = I_2$. So base current doesn't disturb voltage divider action. Thus, Q-point is independent of base current as well as current gain.

Also, V_{BB} is designed to be large enough that small variations in V_{BE} assumed value of won't affect I_E .

Current in base voltage divider network is limited by choosing $I_2 \leq I_C/5$. This ensures that power dissipation in bias resistors is $< 17\%$ of total quiescent power consumed by circuit and $I_2 \gg I_B$ for $\beta > 50$.



Design Guidelines

1. Choose Thevenin equivalent base voltage $\frac{V_{CC}}{4} \leq V_{BB} \leq \frac{V_{CC}}{2}$

2. Select R_1 to set $I_1 = 9I_B$. $R_1 = \frac{V_{BB}}{9I_B}$

3. Select R_2 to set $I_2 = 10I_B$. $R_2 = \frac{V_{CC} - V_{BB}}{10I_B}$

4. R_E is determined by V_{BB} and desired I_C . $R_E \cong \frac{V_{BB} - V_{BE}}{I_C}$

5. R_C is determined by desired V_{CE} .

($V_{CC}/3$ or $\sim V_{CC}/2$ in the absence of R_E , as the case may be) $R_C \cong \frac{V_{CC} - V_{CE} - R_E I_C}{I_C}$



ESc201, Lecture 20: BJT Amplifier (Small signal Model)

Example: Design 4-resistor bias circuit with given parameters.

Given data: $I_C = 750 \text{ mA}$, $\beta_F = 100$, $V_{CC} = 15 \text{ V}$, $V_{CE} = 5 \text{ V}$.

Assumption: Forward-Active operation region, $V_{BE} = 0.7 \text{ V}$

Rule of thumb ($V_{CC}/3$): Divide ($V_{CC} - V_{CE}$) equally between R_E & R_C . or $V_E = 5\text{V}$ & $V_C = 10\text{V}$.

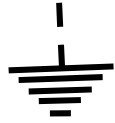
$$\begin{aligned}
 R_C &= \frac{V_{CC} - V_C}{I_C} = 6.67 \text{ k}\Omega & R_E &= \frac{V_E}{I_E} = 6.60 \text{ k}\Omega & \therefore V_B &= V_E + V_{BE} = 5.7 \text{ V} \\
 I_B &= \frac{I_C}{\beta_F} = 7.5 \mu\text{A} & I_2 &= 9I_B = 67.5 \mu\text{A}, & I_1 &= 10I_B = 75 \mu\text{A} \\
 R_1 &= \frac{V_B}{10I_B} = 76 \text{ k}\Omega & R_2 &= \frac{V_{CC} - V_B}{9I_B} = 138 \text{ k}\Omega
 \end{aligned}$$

$$\begin{aligned}
 A_v &= \frac{v_o}{v_i} = \left(\frac{v_o}{v_b} \right) \left(\frac{v_b}{v_i} \right) = - \frac{\alpha i_e R_L}{i_e (r_e + R_E)} \left(\frac{v_b}{v_i} \right) \\
 &= - \frac{\alpha i_e R_L}{i_e (r_e + R_E)} \frac{i_i [R_B \parallel ((\beta + 1)(r_e + R_E))]}{i_i \{R_i + [R_B \parallel ((\beta + 1)(r_e + R_E))]\}} \\
 &\approx - \frac{(\beta / (\beta + 1)) R_L}{(r_e + R_E)} \frac{(\beta + 1)(r_e + R_E)}{\{R_i + (\beta + 1)(r_e + R_E)\}} \\
 &= - \frac{\beta R_L}{\{R_i + r_\pi + (\beta + 1)R_E\}} \\
 &\approx - \frac{\beta R_L}{\{R_i + r_\pi + (\beta + 1)R_E\}} \approx - \frac{\beta R_L}{\{(\beta + 1)R_E\}} \Big|_{R_E \gg r_e}
 \end{aligned}$$

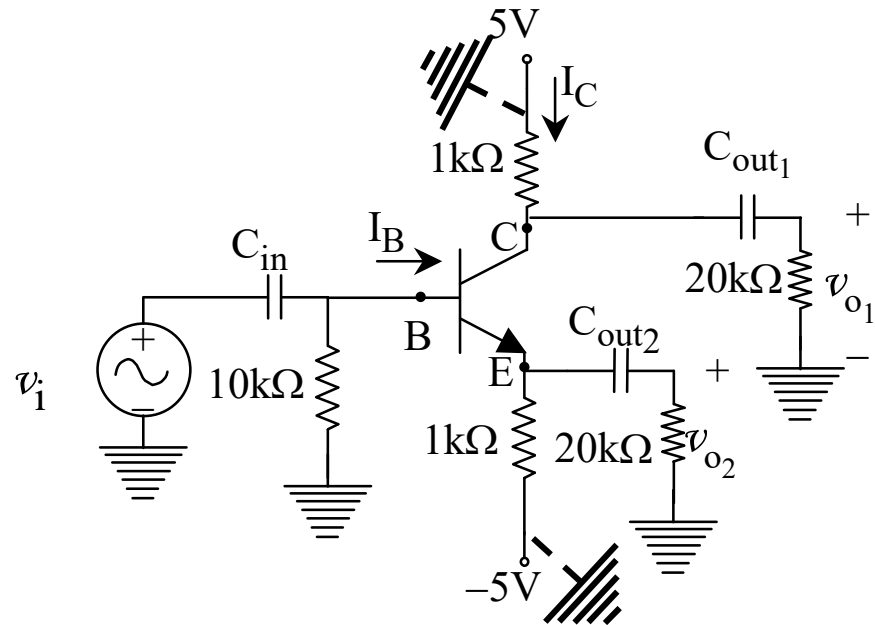
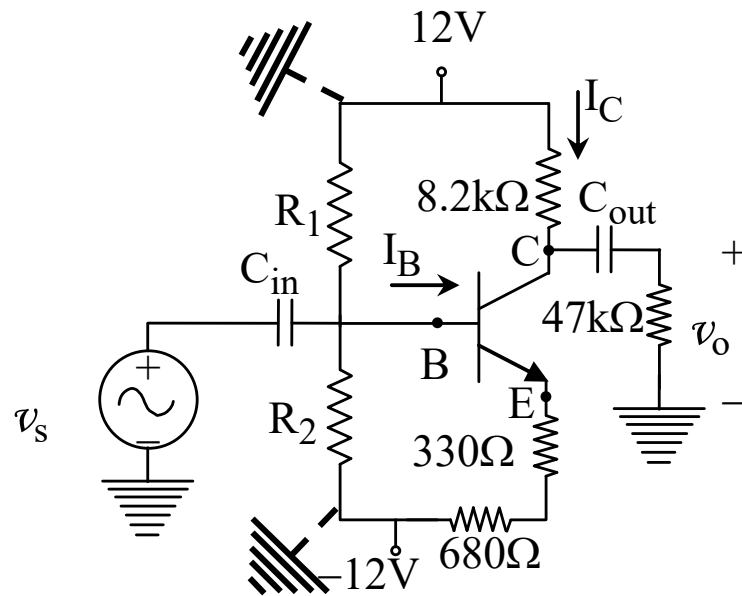
$$\begin{aligned}
 &\frac{A_v(\text{with } R_E)}{A_v(\text{without } R_E)} \\
 &= - \frac{\beta R_L}{\{R_i + r_\pi + (\beta + 1)R_E\}} \\
 &\quad - \frac{\beta R_L}{\{R_i + r_\pi\}} \\
 &\approx \frac{1}{1 + \frac{\beta R_E}{r_\pi}} = \frac{1}{1 + g_m R_E}
 \end{aligned}$$



ESc201, Lecture 19: Bipolar Junction Transistor (Small signal Model)



Signifies short for all A.C. to ground.





ESc201, Lecture 20: BJT Amplifier (Small signal Model)

Class Average:

MiniQ1 → 4.35/10

MiniQ2 → 5.91/10

MiniQ3 → 1.57/10

MajQ1 → 3.23/10



ESc201, Lecture 16: Power Supply

